

Materials-specific theory for Spin Electronics

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Computational Materials Science

Mission:

To understand the magnetic, optical, and electrical properties of condensed matter and the relationship between these physical properties and its chemical composition and atomic structure.

The problem ...

N particle Schrödinger equation

$$\hat{H}\Psi(r_1,r_2,\ldots,r_N)=E\Psi(r_1,r_2,\ldots,r_N)$$

$$\hat{H} = -\frac{\hbar^2}{2m} \sum_{i=1}^{N} \nabla_i^2 + \frac{1}{2} \sum_{i\neq j}^{N} \frac{e^2}{|r_i - r_j|} - \sum_{l=1}^{N} \sum_{i\neq j}^{N} \frac{Z_l e^2}{|r_i - R_l|}$$

If we know Ψ , then we know everything ... but the Schrödinger equation can only be solved exactly for VERY small systems:

analytically for N=1 and quasi 1-D problems (free electron, H atom, harmonic oscillator)
numerically for N small and high symmetry (light atoms, homogeneous electron gas)

Condensed Matter:

N ~ 10²³ electrons/cm³

The solution

"Density Functional Theory"

valid for electronic ground state

Starting point for:

- structure of materials
- magnetism
- dynamics (phonons)
- transport theory
- excitations (optical properties)
 etc.



Reduce linear differential equation for a function in 3N variables to N coupled non-linear integro-differential equations for N functions in 3 variables DFT: For the electronic ground state, the total energy only depends on the electron density

$$E[n] = T[n] + \int \sum_{l} \frac{Z_{l}n(r)}{|r-R_{l}|} dr + \frac{1}{2} \sum \frac{n(r)n(r')}{|r-r'|} dr dr' + E_{xc}[n]$$

Use the variational principle for the ground state energy:

$$\begin{bmatrix} -\frac{\nabla^2}{2} + \upsilon_{eff}(r) \end{bmatrix} \psi_i(r) = \varepsilon_i \psi_i(r)$$
 Kohn-Sham equations of DFT

$$n(r) = \sum_{i}^{N} |\psi_{i}(r)|^{2}$$

electron density

$$\upsilon_{\text{eff}}(r) = \sum_{l} \frac{Z_{l}}{|r-R_{l}|} + \sum_{i\neq j}^{N} \frac{n(r')}{|r-r'|} dr' + \frac{\delta E_{xc}(r)}{\delta n(r)}$$

Effective potential:

Local Density Approximation ... then calculate the total ground state energy

$$E[n] = T[n] + \int \sum_{l} \frac{Z_{l}n(r)}{|r-R_{l}|} dr + \frac{1}{2} \sum \frac{n(r)n(r')}{|r-r'|} dr dr' + E_{xc}[n]$$





Theoretical Methods: ab-initio

Parameter-free: the only input to the calculations are the constants occuring in the Schrödinger Equation: e, h, m_e, c (Dirac eqn)

Translational symmetry

For a solid with N $\sim 10^{23}$ per cm³ we need to make use of translational symmetry to make solution of KSEs tractable.

Use repeated supercells to model:

Amorphous or Liquid phases

Surfaces

Point or

defects

etc.

extended





DFT is a theory for ground state properties. The eigenvalue spectrum yields incorrect values of the gap Doped divalent hexaborides CaB₆ are high temperature magnetic semiconductors

(b) GW

R M

(a) LDA

11.0 LiCl ▲ DFT-L DA GW 9.0 y = GW and DFT-LDA gaps (eV) Energy (eV) 10 7.0 -5 5.0 GaN SiC 3.0 1.0 -15 -1.02.0 6.0 8.0 4.0 10.0 RM МΧΓ ΜΧΓ x = Expt. gaps (eV)

Solve a "quasiparticle" equation use the "GW" approximation

Tromp et al. PRL 87 (2001)

Spin Transport



Giant MagnetoResistance (GMR)

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Transport theory: Landauer-Büttiker



The transmission matrix element $t_{\mu\nu}$ describes the probability amplitude that a state $|\mu\rangle$ in the left lead is transmitted through the scattering region into a state $|\nu\rangle$ in the right lead.



Single clean interface between (almost) perfectly lattice matched Cu and Co

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Ab initio transmission probabilities $T(k_x,k_y)$ for $Cu \rightarrow Co(100)$







Fermi surfaces of fcc-Co: minority-spin





http://www.physik.tu-dresden.de/~fermisur/



- •Electrons can be strongly reflected at a perfect interface (no disorder) between two different metals because of bandstructure mismatch
- •Interface disorder can increase the interface transparency
- •The transmission through an interface into a ferromagnetic material can be strongly spin-dependent





Interface Resistances

$$\frac{1}{R} = G = \frac{e^2}{h} Tr\{t t^+\}$$

AB

But suppose A=B; then $R \neq 0$?

Correction for Sharvin resistance

$$SR_{A/B} = \frac{Sh}{e^2} \left[\frac{1}{tr\{t \ t^+\}} - \frac{1}{2} \left(\frac{1}{N_A} + \frac{1}{N_B} \right) \right]$$

Co/Cu	$f\Omega m^2$	Orientation	majority	minority	Schep et al.
	calculation	(100)	0.33	1.79	FRD 77
	calculation	(111)	0.39	1.46	
	expt (MSU)	(111)	0.26±0.06	1.84±0.14	



Cu/Co fcc(111)	R↑ fΩm²	R↓ fΩm²	
Clean	0.39	1.46	
2x50-50 alloy	0.41	1.82	
Expt (MSU)	0.26±0.06	1.84±0.14	



Xia et al. PRB '01

Applications



•GMR

- •CPP Interface resistances
- ·CIP
- Transport through domain walls
- ·JMR
- •Current induced torque
- Spin injection in Fe/InAs
- Andreev reflection at F/S interfaces
- Enhancement of Gilbert damping



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Measure spin-polarization with F/S point contacts

•Mechanical point contacts Soulen et al. Science **282** (1998)



- Simple
- Flexible
- Poorly characterized

•Thin-film point contacts Upadhyay et al. PRL **81** (1998)



- Well characterized
- Difficult
- Inflexible

Near perfect fit to experiment using BTK theory without any spin dependent interface transparency !



BTK theory:

Model interfacial scattering (of free electrons) by $Z \upsilon_F \delta(x)$

Transmission T = $1/(1+Z^2)$

Spin polarized situation - two parameters: Z, P



Result of scattering theory for F/S interface:

$$G_{FS}(\varepsilon) = \frac{e^2}{h} \sum_{\sigma=\pm 1} Tr(1 - R_{ee}^{\sigma} R_{ee}^{\sigma\dagger} + \frac{R_{he}^{\sigma} R_{he}^{\sigma\dagger}}{R_{he}^{\sigma\dagger}})$$

The conductance only depends on the normal state transmission and reflection matrices.

(1998)

$$R_{ee}^{\sigma} = r_{FF}^{\sigma}(\varepsilon) + \alpha^{2} t_{FN}^{\sigma}(\varepsilon) r_{NN}^{-\sigma^{*}}(-\varepsilon) \frac{1}{1 - \alpha^{2} r_{NN}^{\sigma}(\varepsilon) r_{NN}^{-\sigma^{*}}(-\varepsilon)} t_{NF}^{\sigma}(\varepsilon)$$

and

$$R_{he}^{\sigma} = \alpha^{*} e^{-i\phi} t_{FN}^{-\sigma^{*}}(-\varepsilon) \frac{1}{1 - \alpha^{2} r_{NN}^{\sigma}(\varepsilon) r_{NN}^{-\sigma^{*}}(-\varepsilon)} t_{NF}^{\sigma}(\varepsilon)$$

$$\begin{aligned} |\varepsilon| < \Delta_0 : \alpha = e^{-i \arccos(\varepsilon/\Delta_0)} & \text{Rev. Mod. Phys. 69 (1997);} \\ |\varepsilon| > \Delta_0 : \alpha = \left(\varepsilon - \operatorname{sgn}(\varepsilon) \sqrt{\varepsilon^2 - \Delta_0^2}\right) / \Delta_0, |\alpha| < 1 \\ eI(V) = \int d\varepsilon \left[f(\varepsilon) - f(\varepsilon + eV) \right] G_{FS}(\varepsilon) \end{aligned}$$

Large lattice mismatch





Because of the large lattice mismatch we use a lateral supercell with 3x3 Pb atoms to match to 4x4 Cu (Ni, Co) atoms or 4x4 Pb atoms to match to 5x5 Cu (Ni, Co) atoms.

Pb: 4x4 Cu: 5x5



Model disorder in lateral supercells as two layers of alloy.

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Andreev Reflection

Results: V=0

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$G_{FS}(0)/G_{FN}(0)$	Cu/Pb	Ni/Pb	Co/Pb
Clean	1.54	1.29	1.08
Rough	1.36	1.16	1.00
Expt.	1.38	1.18	1.13



RMS

O Co Ni



Distribution function of tranmission matrix eigenvalues



Conclusions



The good agreement obtained fitting theory with a simple generalization of BTK theory to ferromagnets is misleading (also Lancaster group).

The spin-dependent transmission through an A/B interface $T_{A/B}$ is a property of the interface and cannot be factored into an A part and a B part characteristic of the bulk materials.

BTK theory doesn't describe transport at a F/S interface and needs to be extended - include Zeeman splitting in fringing fields?

Molecular Electronics





Work done in collaboration with:

- <u>Twente</u> K. Xia (Beijing) M. Zwierzycki S. Gerritsen M. Talanana
- I. Turek (Brno)

<u>Delft</u> G.E.W. Bauer A. Brataas (Harvard, Trondheim) <u>Philips</u> K. Schep J. van Hoof





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The End



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